Amendments to th Sp cification:

On pag 1, immediat ly following the title, please insert the following paragraph:

--This is a continuation of US Patent Serial No.10/142,587, filed on 9 May 2002.--

Please delete the final two paragraphs of page 4, beginning on line 26, in their entirety, and add the following four paragraphs in their place:

FIG. 1 illustrates a TFT structure in a first stage of preparation before irradiation of a resist layer.

FIG. 2 illustrates a TFT structure in a second stage of preparation during irradiation by a beam directed at a first angle.

FIG. 2A illustrates a TFT structure in a second stage of preparation during irradiation by a beam directed at a second angle.

FIGS. 3 through 5 illustrate the development and further processing of the TFT structure as irradiated according to the embodiment of FIG. 2.

Please replace the second full paragraph of page 7 (lines 22-30) with the following rewritten paragraph:

In Figs. 1 to 5, the TFT formation process has been shown as creating a TFT structure alongside ~~one edge 16A~~ both opposing edges 16A and 16B of the gate electrode 2 ~~for clarity~~. ~~However, a corresponding structure would in practice be~~ The two structures thus simultaneously formed alongside the opposing edges 16A and 16B ~~which~~ may be desirable in some applications. It may also be preferable to ~~inhibit the~~ formation a single such structure rather than ~~of such a corresponding~~ two symmetrical structures, for example when fabricating an AMLCD. This may be achieved for example by altering the angle of incidence of the radiation 18A to which the negative resist is exposed such that only one edge 20A is shadowed as illustrated in FIG. 2A.